

**IN THE CLAIMS:**

Please cancel claims 7, 9-10 and 13-19 without prejudice to or disclaimer of the subject matter recited therein.

Please amend claims 1-6, 8, 11 and 12 as follows:

**LISTING OF CURRENT CLAIMS**

Claim 1. (Currently Amended) A light-emitting semiconductor device ~~having enhanced brightness~~, comprising:

- (a) a semiconductor substrate;
- (b) an active layer located above the semiconductor substrate, for inducing illumination of light;
- (c) a conductive back contact located below the semiconductor substrate;
- (d) ~~a conductive front contact located above the active layer, the front contact including a metallic bonding pad and ohmic contact having a minimum dimension ranging between 0.1 and 5 micrometers and distributed above the active layer; a capping layer formed on the active layer;~~
- (e) an ohmic contact metallic mesh pattern having line width between about 0.1 to 4 micrometers formed on the capping layer; and
- (f) a metallic bonding pad formed on the ohmic contact metallic mesh pattern.

Claim 2. (Currently Amended) The light-emitting semiconductor device ~~having enhanced brightness~~ of Claim 1, wherein the semiconductor substrate is GaAs.

Claim 3. (Currently Amended) The light-emitting semiconductor device ~~having enhanced brightness~~ of Claim 2, wherein the active layer is AlGaInP.

Claim 4. (Currently Amended) The light-emitting semiconductor device ~~having enhanced brightness~~ of Claim 2, wherein the active layer is AlGaAs.

Claim 5. (Currently Amended) The light-emitting semiconductor device ~~having enhanced brightness~~ of Claim 1, wherein the semiconductor substrate is sapphire.

Claim 6. (Currently Amended) The light-emitting semiconductor device ~~having enhanced brightness~~ of Claim 4, wherein the active layer is AlGaInN.

Claim 7. (Canceled)

Claim 8. (Currently Amended) The light-emitting semiconductor device ~~having enhanced brightness~~ of Claim 1, wherein the ~~metallic patterns of the front contact is configured to an interconnected mesh and~~ ohmic contact metallic mesh pattern ~~is~~ in electrical connection with the metallic bonding pad.

Claims 9-10. (Canceled)

Claim 11. (Currently Amended) The light-emitting semiconductor device ~~having enhanced brightness~~ of Claim 7, ~~1, wherein the metallic patterns of the front contact are embedded and interconnected in an ITO layer.~~ further comprising an ITO layer formed in between the capping layer and the metallic bonding pad so that the ohmic contact metallic mesh pattern is embedded in the ITO layer.

Claim 12. (Currently Amended) A light-emitting device, comprising:

- (a) a substrate;
- (b) an active layer located above the substrate, for inducing generation of light;
- (c) a back contact located below the substrate;
- (d) ~~a front contact located above the active layer, the front contact including a metallic bonding pad and ohmic contact metallic patterns, the metallic patterns of the front contact having a minimum dimension ranging between 0.1 and 5 micrometers and distributed above the active layer.~~ capping layer formed on the active layer;

- (e) an ohmic contact metallic pattern formed on the capping layer wherein the ohmic contact metallic pattern is in a form selected from the group consisting of a number of fingers, meshes, and dots, further the dots sizes or line width of meshes or fingers is between 0.1 micrometer and 4 micrometers;
- (f) an ITO (indium tin oxide) layer formed on the capping layer and the ohmic contact metallic pattern; and
- (g) a metallic bonding pad formed on the ITO layer.